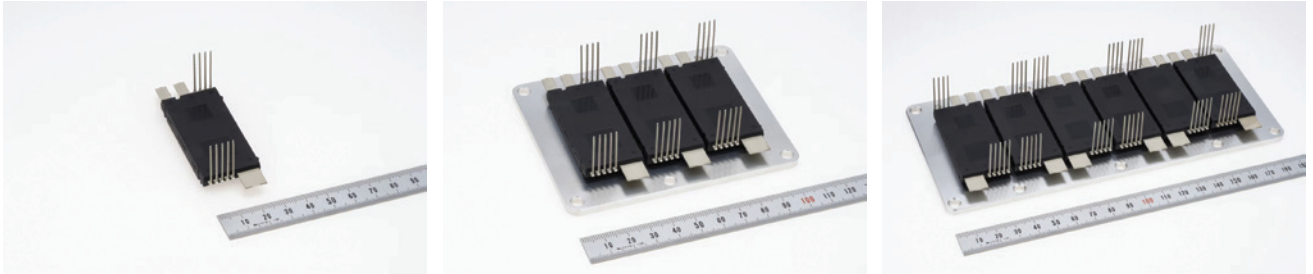


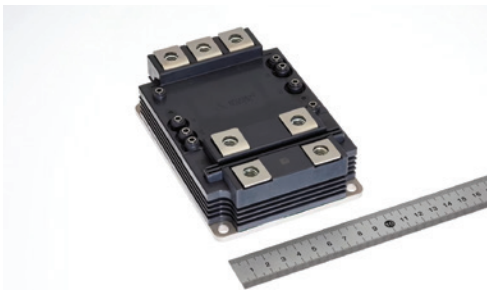
Mitsubishi Electric Power Semiconductor Devices

J3-Series SiC and Si Power Semiconductor Modules for xEVs



The J3-Series SiC and Si power semiconductor modules for electrified vehicles (xEVs) feature about 60% smaller size than existing modules. These are SiC-MOSFETs designed for electric vehicles (EVs) and plug-in hybrid vehicles (PHEVs) and offer extended range and lower electricity costs. The J3-Series is available in comprehensive lineup and can be combined with J3-T-PM products for scalable xEV inverter designs.

SBD-embedded SiC-MOSFET Module Unifull™ for Railways, Electric Power Systems and More



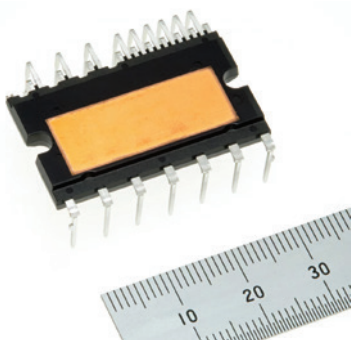
New 3.3kV/400A and 3.3kV/200A versions of Mitsubishi Electric’s SBD-embedded SiC-MOSFET module, together with the existing 3.3kV/800A, comprise the new Unifull™ series.

SBD-embedded SiC-MOSFETs contribute to inverter output, efficiency and reliability.

NX-type Full-SiC Power Semiconductor Modules for Industrial Equipment



Specifically, the NX-type full-SiC power semiconductor modules feature optimized electrode structure and SiC chip. Thus, they contribute to more efficient, smaller and lighter equipment. Moreover, compatibility to the NX-type package allows new modules to easily replace current version.



SLIMDIP™ Series for Home Appliances

The SLIMDIP™ Series offers 30% smaller package size compared to Super Mini DIPIM™. This results from the integration of an Reverse Conducting IGBT (RC-IGBT), which implements the thin wafer structure of the 7th generation IGBT. Also, it has a built-in control IC with protection functions and a BSD with a current-limiting resistor that reduces the number of components. The maximum guaranteed case temperature has been extended to 115°C for greater flexibility in heat dissipation design.